# NSN 5962-01-491-2679

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# **Operating Tempurature Range:**

-55.0/+125.0 degrees celsius

# Storage Tempurature Range:

-65.0/+155.0 degrees celsius

# **End Application:**

Radar threat emitter an/mst-t1; m3p reu-l

## Features Provided:

High speed and low power and asynchronous

## **Inclosure Material:**

Ceramic

# Inclosure Configuration:

Dual-in-line

#### **Output Logic Form:**

Complementary-metal oxide-semiconductor logic

#### **Product Name:**

Cmos asynchronous fifo

## Voltage Rating And Type Per Characteristic:

-0.5 volts power source and 7.0 volts power source

## **Time Rating Per Chacteristic:**

20.00 nanoseconds af output megawatts

# Memory Device Type:

First-in first-out

## **Special Features:**

2, 048 x 9-bit; thin ceramic dip

#### **Test Data Document:**

96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

#### **Terminal Type And Quantity:**

28 printed circuit

## Shelf Life:

N/a

#### Unit Of Measure:

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# Demilitarization:

Yes - demil/mli

Fiig:

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